MOSFETs Silicon N-Channel MOS

# SSM6N62TU

### 1. Applications

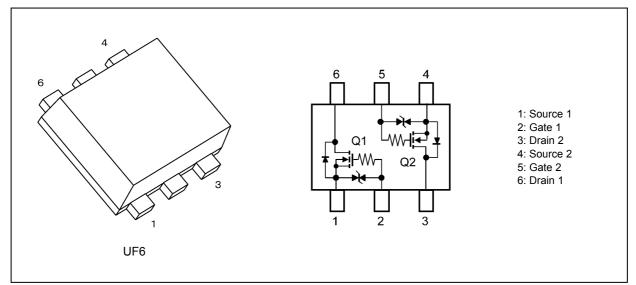
- Power Management Switches
- DC-DC Converters

### 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 1.2-V drive
- (3) Low drain-source on-resistance
  - :  $\mathrm{R}_{\mathrm{DS(ON)}}=67~\mathrm{m}\Omega$  (typ.) (@V\_{\mathrm{GS}}=4.5~\mathrm{V})
  - $R_{\rm DS(ON)}=74~m\Omega$  (typ.) (@V\_{\rm GS}=2.5~V)
  - $\mathrm{R}_{\mathrm{DS(ON)}}=84~\mathrm{m}\Omega$  (typ.) (@V\_{\mathrm{GS}}=1.8~\mathrm{V})
  - $R_{\rm DS(ON)}$  = 94 m $\Omega$  (typ.) (@V\_{\rm GS} = 1.5 V)

 $R_{\rm DS(ON)}$  = 121 mO (typ.) (@V\_{\rm GS} = 1.2 V)

### 3. Packaging and Pin Assignment



### 4. Orderable part number

Orderable part number	AEC-Q101		Note			
SSM6N62TU,LF	—		General Use			
SSM6N62TU,LXGF	YES	(Note 1)	Unintended Use	(Note 1)		
SSM6N62TU,LXHF	YES		Automotive Use			

Note 1: For more information, please contact our sales or use the inquiry form on our website.

### Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	20	V
Gate-source voltage		V <sub>GSS</sub>	±8	
Drain current (DC)	(Note 1)	Ι <sub>D</sub>	0.8	A
Drain current (pulsed)	(Note 1), (Note 2)	I <sub>DP</sub>	1.6	]
Power dissipation	(Note 3)	PD	500	mW
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Pulse width (PW)  $\leq$  10 s, duty  $\leq$  1%

- Note 3: Device mounted on an FR4 board. (PD for the entire IC) (FR4, 25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 645 mm<sup>2</sup>)
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 6. Electrical Characteristics

### 6.1. Static Characteristics (Unless otherwise specified, $T_a = 25$ °C) (Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±8 V	_	_	±10	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V		_	1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V	20	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = -5 V	15	_	—	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 1 mA	0.4	0.6	1.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 1.2 V	_	121	456	mΩ
			I <sub>D</sub> = 200 mA, V <sub>GS</sub> = 1.5 V	_	94	173	
			I <sub>D</sub> = 600 mA, V <sub>GS</sub> = 1.8 V		84	120	
			I <sub>D</sub> = 800 mA, V <sub>GS</sub> = 2.5 V	_	74	98	
			I <sub>D</sub> = 800 mA, V <sub>GS</sub> = 4.5 V		67	85	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 200 mA		3.0	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 2: Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

### 6.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25 \text{ °C}$ ) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,	_	177	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	17	_	
Output capacitance	C <sub>oss</sub>		_	52	_	
Switching time (turn-on time)		V <sub>DD</sub> = 10 V, I <sub>D</sub> = 800 mA,	-	332	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to 4.5 V, $R_{G}$ = 50 $\Omega$		2653	_	

#### 6.3. Switching Time Test Circuit

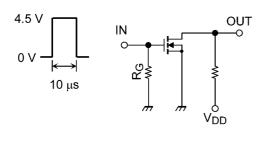


Fig. 6.3.1 Switching Time Test Circuit

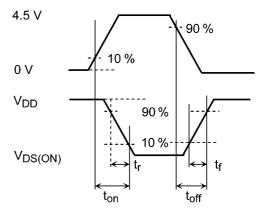


Fig. 6.3.2 Input Waveform/Output Waveform

## 6.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25$ °C) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = 10 V, I <sub>D</sub> = 800 mA,	_	2.0		nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = 4.5 V	_	1.3	_	
Gate-drain charge	Q <sub>gd</sub>		_	0.6	_	

## 6.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{\text{DSF}}$	$I_{\rm D}$ = -800 mA, $V_{\rm GS}$ = 0 V	—	-0.6	-1.2	V

Note 1: Pulse measurement.

### 7. Marking

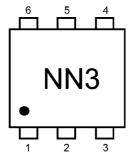
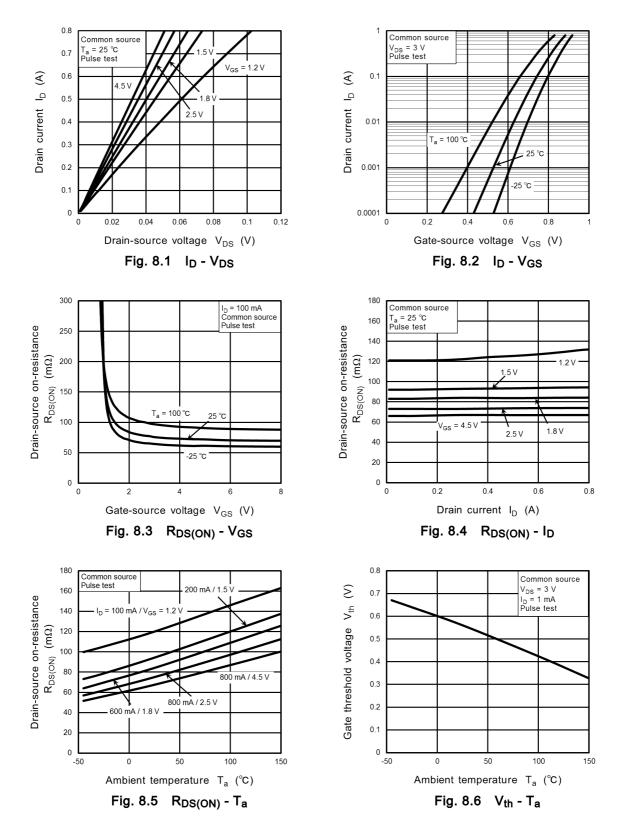
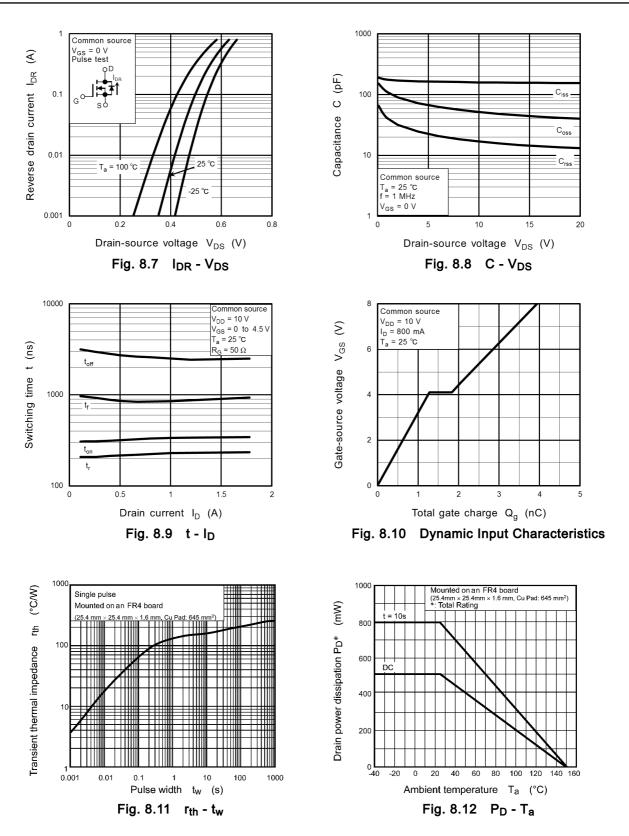


Fig. 7.1 Marking

### 8. Characteristics Curves (Q1,Q2 Common) (Note)





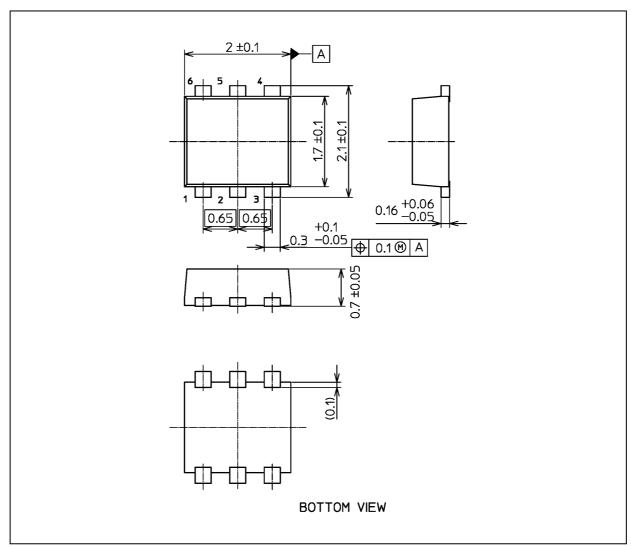
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### SSM6N62TU

### **Package Dimensions**

Unit: mm



Weight: 7.0 mg (typ.)

Package Name(s) Nickname: UF6

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